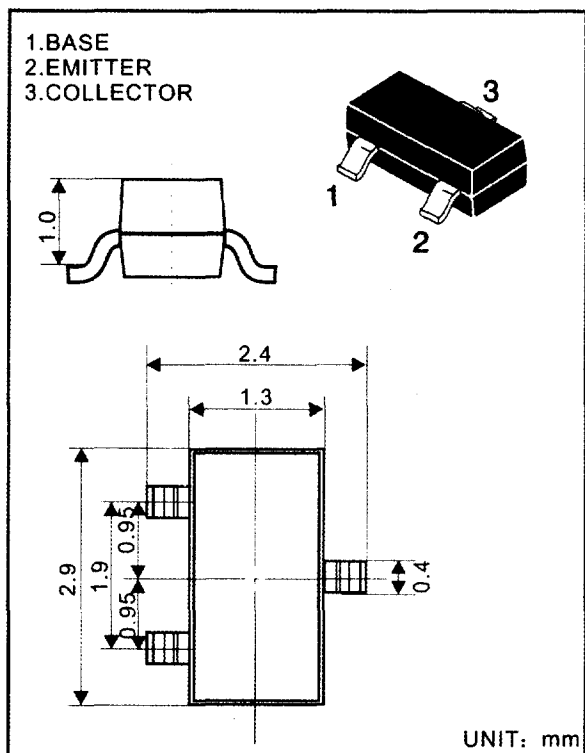


SOT-23 Plastic-Encapsulate Transistors

MMBT4403LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

PCM: 0.3 W (Tamb=25°C)

Collector current

ICM: -0.6 A

Collector-base voltage

V(BR)CBO: -40V

Operating and storage junction temperature range

TJ, Tstg: -55°C to +150°C

ELECTRICAL CHARACTERISTICS

(Tamp=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Drain-source Breakdown Voltage	V(BR)CBO	IC=-100 μA, IE=0	-40		V
Collector Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, IB=0	-40		
Emitter-base Breakdown Voltage	V(BR)EBO	IE=-100 μA, IC=0	-5		
Collector Cut-off Current	ICBO	VCB=-35V, IE=0		-0.1	μA
	ICEO	VCE=-35V, IB=0		-0.1	
Emitter cut-off current	IEBO	VEB=-4V, IC=0		-0.1	μA
DC Current Gain	HFE	VCE=-2V, IC=-150mA	100	300	
Collector-emitter Saturation Voltage	VCEsat	IC=-150mA, IB=-15mA		-0.4	V
Base-emitter Voltage	VBEsat	IC=-150mA, IB=-15mA		-0.95	V
Transition Frequency	ft	VCE=-10V, IC=-20mA f=100MHz	200		MHz

DEVICE MARKING : MMBT4403LT1:2T

Typical Characteristics

MMBT4403LT1

Static Characteristics

